

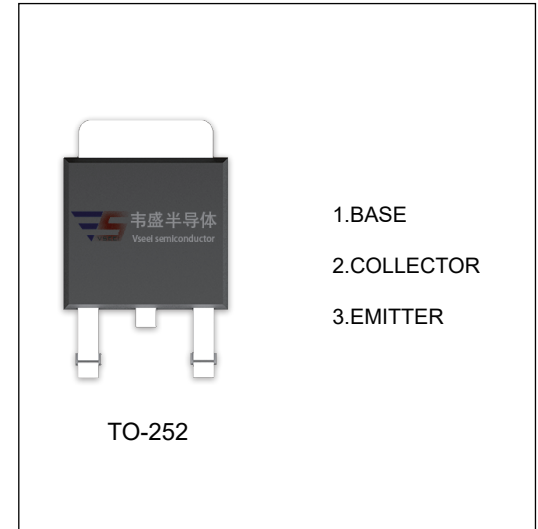
2SD1815 TRANSISTOR (NPN)

FEATURES

- Low Collector-to-Emitter Saturation Voltage
- Excellent Linearity of h_{FE}
- High f_T
- Fast Switching Time

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise note)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	3	A
P_C	Collector Power Dissipation	1	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=100\text{V}, I_E=0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=5\text{V}, I_C=500\text{mA}$	70		400	
	$h_{FE(2)}$	$V_{CE}=5\text{V}, I_C=2\text{A}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1.5\text{A}, I_B=150\text{mA}$			0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1.5\text{A}, I_B=150\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=500\text{mA}$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		25		pF
Turn-on time	t_{on}	$V_{CC}=50\text{V}, I_C=1.5\text{A}, I_{B1}=-I_{B2}=-0.15\text{A}$		100		nS
Storage time	t_s			900		nS
Fall time	t_f			50		nS

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R	S	T
Range	70-140	100-200	140-280	200-400